

PERSONAL INFORMATION

Fernando Genova



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Sex Male | Date of birth 11 July 1951 | Nationality Italian

PREFERRED JOB

Smart Energy Engineering / Environmental sensor networks and metering

WORK EXPERIENCE

2006 – 2011

Deputy Mayor of the Town of Pianezza

In addition to his business in Telecom Italia, from 2006 to 2011 Fernando Genova served his country as Deputy Mayor and Councillor for Urban Planning and Land Policy in the town of Pianezza, where he lives.

He put main attention to the land preservation (approval of a new Master Plan of the Town) and to the Energy Efficiency of the public utilities

2005 – 2009

Senior Project manager in the Research & Trends Area at Telecom Italia Lab (TILab)

Turin (Italy)

Head of the Innovation Lab of the Research & Trends Area

He devoted most of his activity to the development of very low cost Wireless Sensor Networks to monitor and improve the energy savings in Telecom Italia Switching Plants and data centers.

2000 – 2004

Head of of the Materials and Environment Area at TILab

The Area mission was the study and development of new materials and their environmental footprint when used in Telecom Italia network. The annex Lab was equipped with most of facilities for a complete chemical and physical characterization. In the Area worked about 30 people.

Strong effort was put in the development of low cost environmental tele-monitoring systems for indoor and outdoor air quality (participation at the European ADA Project)

1996 – 1999

Head of the Materials Innovation and Testing Group at TILab

In addition to the routine activity on new materials and devices conformity tests, a Lab was set-up to validate and evaluate chip cards for e-commerce and SIM cards for mobile communication

1994 – 1995

Head of the Telecom Italia Incoming Quality Laboratory

In less than one year the lab (three departments and 50 people), achieved the Accreditation from three different Accreditation Bodies (SINAL, CIMECO and P&T Ministry).

Lab facilities allowed to perform conformity test in three areas: Materials, Transmission and electronic devices, Acoustics and voice quality

1979 – 1993

Researcher at CSELT (Italian Telecommunication Research Center) in the Optoelectronic & Photonic Department

Turin (Italy)

Responsible for the Epitaxy Crystal Growth (on III-V semiconductors) Lab.

Specialist in Molecular Beam Epitaxy (MBE) and Metal Organic Chemical vapor deposition (MOCVD). In this field he highly contributed to the development and realization of Semiconductor Integrated Optical Devices of innovative conception.

1976 – 1978 Researcher at CNR (Italian National Centre for the Research)

Turin (Italy)

Montecarlo simulation and data analysis for experiments carried on at CERN in the High Energy Particle Physics field.

Stage at CERN under the supervision of prof. C. Rubbia

EDUCATION AND TRAINING

2011 – 2012 Perfectioning Course in Energetics

Politecnico, Turin

The program covered all the relevant aspects of Energetics and in particular:

Energy sources, carriers and production.

Power plants, power use and energy efficiency.

Enviromental effects of energy production and use

2005 – 2005 Advanced training course in Networking

Telecom Italia Learning Service

2002 – 2003 Qualified Expert in Radiation Protection - Level I

Ministry of Labour and Productive Activities, Rome (Italy)

Certification N. 481 of the Italian Register

1971 – 1976 Degree in Physics (cum Laude)

University of Turin, Faculty of Mathematics, Physics and Natural Sciences, (Italy)

Address of studies mainly theoretical

Specialization:

High Energy Particle Physics

Solid State Physics

PERSONAL SKILLS

Mother tongue(s) Italian

Other language(s)

	UNDERSTANDING		SPEAKING		WRITING
	Listening	Reading	Spoken interaction	Spoken production	
English	B1	C1	C1	C1	C1
French	B1	B1	B2	B2	B2

Levels: A1/A2: Basic user - B1/B2: Independent user - C1/C2: Proficient user
[Common European Framework of Reference for Languages](http://www.cerl.eu)

Communication skills

Ggood communication skills gained through my experience in business meeting and my participation to Scientific Conferences as speaker or session chairman

Skills were acquired also through the participation to training courses on management and communication organized by my company.

Organisational / managerial skills	Leadership: for most of my career I was responsible for a team ranging in size from 10 to 50 people; Project Management: I usually have managed projects of or tasks of high technical complexity (often for international cooperations) in the R&D field
Job-related skills	Good command of quality control processes: In 1994 I was responsible for the Accreditation to the ISO45000 standard of the Income Quality Test Laboratory of Telecom Italia In the following years I always was responsible for a ISO9001 Standard compliant R&D laboratory (many conformity tests were accredited)
Computer skills	Good command of Office suite (word processor, spreadsheet, presentation program) Knowledge in use of Mathcad and Mathematica programs Basic knowledge in Java programming

ADDITIONAL INFORMATION

Publications In my scientific career I've published over 30 among papers and memories (presented at International Conferences, as regular or invited speaker). I have been a member of several International Conference Scientific and Program Committees and I was session chairman in several of them.

[Related document\(s\):](#)

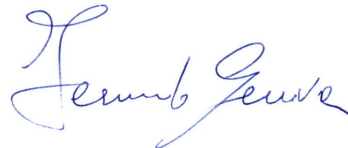
Hobbies Photography, alpine hiking, skiing, diving, theater, bricolage

ANNEXES

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Autorizzo il trattamento dei dati personali ai sensi del D.Lgs. 196/2003

In fede



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Publication list

Fernando Genova

Sorrentino M., Rizzo G., Gaspardone M., Genova F: “Sviluppo e validazione sperimentale di modelli matematici finalizzati ad una gestione efficiente dei sistemi di condizionamento nelle centrali Telecom”, 65° Congresso nazionale ATI, Domus De Maria (Cagliari), 13-17 Settembre 2010, vol. 65o Congresso Nazionale ATI - Atti del Congresso, ISBN:9788890411632

Marco Sorrentino, Gianfranco Rizzo, Fernando Genova, Marco Gaspardone: “A model for simulation and optimal energy management of Telecom switching plants”, Applied Energy Applied Energy, 87 (2010) 259–267

F. Genova, F. Bellifemine, M. Gaspardone: “Thermal and energy management system based on low cost Wireless Sensor Network Technology, to monitor, control and optimize energy consumption in Telecom Switch Plants and Data Centres” presented at the 4th International Telecommunication Energy Special Conference (Telescon 2009). Vienna, Austria, May 10 - 12, 2009

F. Genova: “Optimal energy management of TLC plants, using low cost Wireless Sensor Network based monitoring system and a simulation model for data analysis” Invited at International Telecommunication Energy Conference Songdo Convensia, Incheon, Korea, October 18-22, 2009 (Intelec 2009)

F. Genova, F. Bellifemine, M. Gaspardone, S. Gamarino: “Low cost sub-metering system based on Wireless Sensor Network Technology (to monitor, design, and evaluate energy saving actions in Telecom Plants and Data Centres)”, Metering, Billing / CRM Europe 2008, September 22 – 24, 2008 Amsterdam

Fernando Genova: "Industry perspectives on Ad Hoc and Sensor Networks" invited at DIWANS Workshop, Florence, June 29th, 2004

Fernando Genova, L. Giacomello, M. Parvis, S. Cappellazzo, A. Pedè: "Progetto ADA: un'architettura innovativa per la gestione di reti di monitoraggio", Invited at the 9th National Conference on Sensors and Microsystems (AISEM), Ferrara, February 8-11, 2004

Fernando Genova: "ADA System: an innovative architecture for telemonitoring networks", IST ADA Project presentation at 9th International Conference on Harmonisation within Atmospheric Dispersion Modelling for Regulatory Purposes (Harmo), Garmish, Germany, 1-4 June 2004

S Mosso, S Romussi, F Genova, S Sampò, S Bonetta, S Bonetta, E Carraro "Sviluppo di un metodo per la valutazione della qualità microbiologica dell'aria Indoor", Metrologia e Qualità, Torino, 26-27 Febbraio 2003

Antolini A., Bradley P.J., Cacciatore C., Campi D., Gastaldi G., Genova F., Iori M., Lamberti C., Morello G., Papuzza C., and Rigo C.: "Investigation of interface abruptness in CBE-grown InGaAs/InP QW structures "; IEEE J Elect. Mat. 21 (1992) 233

Genova F., Antolini A., Francesio L., Gastaldi L., Lamberti C., Papuzza C. and Rigo C.: "Influence of the growth parameters on the interface abruptness in CBE grown InGaAs/InP QWs and SLs"; J. Crystal Growth, 120 (1992) 333

Bradley P.J., Calvani R., Campi D., Caponi R., Genova F.: "Nonlinear absorption and refraction in strained InGaAs/InP multiple quantum wells for all optical switching"; Semicond. Sci. Technol., 7 (1992) 552.

G. Morello, F. Genova G. Autore and L. Gastaldi: "CBE growth of InGaAs for optoelectronic applications"; J. Crystal Growth , 107 (1991) 1065.

C. Ghezzi, A. Parisini, L. Tarricone, J. Filipowicz and F. Genova : "Exciton transitions and Photovoltaic spectra in GaAs/AlGaAs multiple Quantum-Wells" ; Mat. Science and Engineering, B9 (1991) 301.

Antolini A., Bradley P.J., Cacciatore C., Campi D., Gastaldi G., Genova F., Iori M., Lamberti C., Morello G., Papuzza C., and Rigo C.: "CBE-grown InGaAs/InP QW structures: an extensive investigation"; Third Int. Conf. on InP and Rel. Mat. Cardiff, 8-13 April 1991, Conf. Proceedings IEEE Catalog #91CH2950-4, pag. 359.

C. Bocchi, C. Ferrari, P. Franzosi, F. Genova, R. Gleichmann, B. Jenichen, C. Rigo and G. Salviati: "Crystal defects in InGaAlAs layers grown on InP substrates by Molecular Beam Epitaxy"; J. Crystal Growth , 106 (1990) 665.

P. Franzosi, M. Scaffardi, F. Genova, C. Rigo, and A. Stano: "Experimental study of misfit dislocations in InP-based heterostructures"; Material Letters, 7, (1989), 1.

A. V. Drigo, A. Aydinli, A. Carnera, F. Genova, C. Rigo, C. Ferrari, P. Franzosi and G. Salviati: "On the mechanism of strain release in MBE grown InGaAs/GaAs single heterostructures"; J. Appl. Phys., 66 (1989), 1975.

F. Genova : " MBE growth and characterization of ternary and quaternary semiconductor alloys and heterostructures "; in "Excitons in Confined Systems " edited by A. Del Sole, A. D'Andrea and A. Lapicciarella; Proceedings in Physics 25, Springer-Verlag

F. Genova : " MBE technology for multistructure optoelectronic and integrated optics devices " ; CSELT Technical Reports , 15, (1988) ,475. Invited Paper at " The thirteenth Conference on Optical Communication " ECOC 87, Helsinki.

A. Aydinli , M. Berti , A. v. Drigo , C. Ferrari , G. Salviati , F. Genova , L. Moro : " Lattice relaxation in InGaAs/ GaAs strained layers " ; Gallium Arsenide and Related Compounds 1987.

P. Franzosi, G Salviati, M. Scaffardi and F. Genova, S. Pellegrino and S. Stano: " Cracks in InP-based heterostructures " ; J. Crystal Growth , 88 , (1988) , 135.

V. Ghergia, P. Cinguino, F. Genova , F.Tosco : " InP-based integrated optoelectronics: activity in the framework of the Esprit programme " ; CSELT Technical Reports, 16, (1988), 105. Reprint from " Globecom 87 ", Tokyo, Nov. 87.

F. Genova , G . Morello and C. Rigo : " Molecular beam epitaxy growth of In_{0.53}(Ga_xAl_{1-x})_{0.47}As quaternary layers for optointegrated devices " , J. Vac. Sci. Technol. , B5 , (1987) , 811.

P.Cinguino , F.Genova , S. Morasca , C.Rigo and S.Stano : " Low loss ridge optical waveguides in quaternary InGaAlAs/ InP grown by MBE " ; Electron. Lett. , 23 , (1987) , 235

P.Cinguino , F.Genova , C.Rigo , C. Cacciatore and S.Stano : " Monolithic integrated InGaAlAs/ InP ridge waveguide photodiodes for 1.55 μ m operation grown by molecular beam epitaxy " ; Appl. Phys. Lett. , 50 , (1987) , 1515.

A. Aydinli , A. Carnera, A. v. Drigo, F. Genova , L. Moro, C. Ferrari, P. Franzosi: "Tetragonal distortion and critical thickness in MBE grown strained layers " ; Revue de Physique, 16, (1987), 193.

M. Berti , A . Carnera , A . V. Drigo , F.Genova , C.Papuzza and C.Rigo : " Structural Characterization of InGaAs/ GaAs strained superlattices grown by MBE on GaAs substrates ; Revue de Physique , (1985) , 227.

P. Franzosi , G. Salviati , F. Genova , S. Stano and F . Taiariol : " Misfit dislocations in InGaAs/ InP MBE single heterostructures " ; J. Crystal Growth , 75 , (1986) , 521.

P.Cinguino , F.Genova , C.Rigo and S.Stano : " Low dark current InGaAs P.I.N. photodiodes grown by molecular beam epitaxy " ; Electron. Lett. , 21 , (1985) , 139.

F.Genova , C.Rigo and S.Stano : " Molecular beam epitaxy growth of InGaAs and AlInAs layers for photodiodes " ; CSELT Technical Reports , 13 , (1985) , 107.

P. Franzosi , G. Salviati , F. Genova , S. Stano and F. Taiariol : " On the location of the misfit dislocations in InGaAs/ InP MBE single heterostructures " ; Materials Lett. , 3 , (1985), 425.

F.Genova , C.Rigo and S.Stano : " Growth of InGaAs layers on InP substrates for I.R. detectors by MBE " ; Mat. Chem. and Phys. , 11, (1984) , 135.

F.Genova , C.Papuzza , C.Rigo and S.Stano : " Effect of InP thermal degradation on MBE InGaAs layers " ; J. Crystal Growth , 69 , (1984) , 63.

C. Papuzza, L.Benassi, D.Campi, F.Genova, C.Rigo and F.Taiariol : "Energy gap in InGaAs MBE layers: dielectric model calculation and experimental values", CSELT Technical Reports, 9, (1981) , 421